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(54) POLISHING SLURRY AND ITS USE

## (57)Abstract:

PROBLEM TO BE SOLVED: To provide polishing slurry which is especially useful as a polishing agent for an insulated dielectric layer in shallow trench isolation(STI) in a manufacturing process of a semiconductor or an IC.

SOLUTION: The polishing slurry to be used in a manufacturing process of a semiconductor or an integrated circuit(IC) contains cerium oxide, hydroxide of aluminum, cerium salt and water, and arbitrarily acid substance for adjusting pH of the slurry less than 5.

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## LEGAL STATUS

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